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**INDUSTRY STANDARD OF THE
PEOPLE'S REPUBLIC OF CHINA**

SJ/T 11975-2025

**Specification for press-fit insulated gate bipolar transistors
(IGB Ts) for power systems
(English Translation)**

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What this standard covers

This standard specifies the terms and definitions, models, dimensions, ratings, characteristic values, inspection rules, marking, packaging, transportation, and storage requirements for press-fit insulated gate bipolar transistors (IGBTs) for power systems. This document applies to press-fit IGBTs for power systems, with or without diodes.

Document data

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